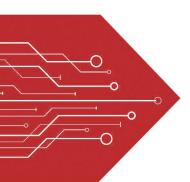
MSKSEMI















ESD

TVS

TSS

MOV

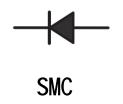
GDT

PLED

Broduct data sheet







FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.21 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature uniess otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

P/N(MARK)	US3A	US3B	US3D	US3E	US3G	US3J	US3K	US3M	UNITS
Maximum Recurrent Peak Reverse Voltage		100	200	300	400	600	800	1000	V
Maximum RMS Voltage		70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current									
t Ta=55°C 3.0				Α					
Peak Forward Surge Current, 8.3 ms single half sine-wave									
superimposed on rated load (JEDEC method) 10			00				Α		
Maximum Instantaneous Forward Voltage at 3.0A		1.0 1.3 1.85				V			
Maximum DC Reverse Current Ta=25°C				1	0				μА
at Rated DC Blocking Voltage Ta=100°C	200			μА					
Maximum Reverse Recovery Time (Note 1)		50 75					nS		
Typical Junction Capacitance (Note 2)		75					pF		
Operating and Storage Temperature Range T _J , Ts _{TG}		-65—+150					°C		

NOTES:

- 1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.



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RATING AND CHARACTERISTIC CURVES (US3A THRU US3M)

FIG.1-TYPICAL FORWARD

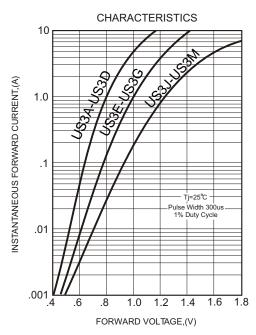
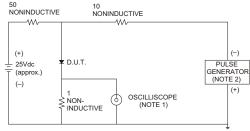


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE
RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

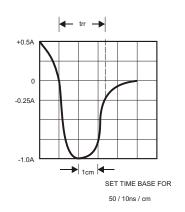


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

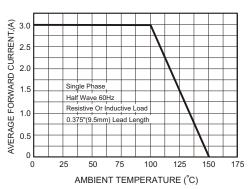


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

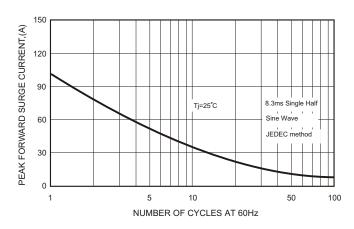
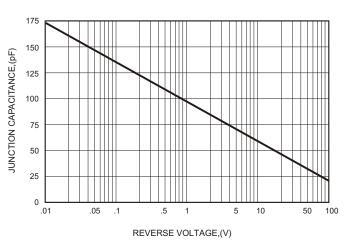


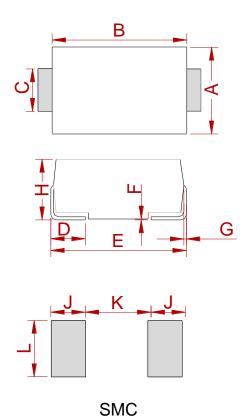
FIG.5-TYPICAL JUNCTION CAPACITANCE





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PACKAGE MECHANICAL DATA



	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	5.75	6.25	0.226	0.246		
В	6.90	7.40	0.272	0.291		
С	2.75	3.25	0.108	0.128		
D	0.95	1.52	0.037	0.060		
E	7.70	8.20	0.303	0.323		
F	0.051	0.203	0.002	0.008		
G	0.15	0.31	0.006	0.012		
Н	2.15	2.62	0.085	0.103		
J	2.40		0.094			
K		4.20		0.165		
L	3.30		0.130			

REEL SPECIFICATION

P/N	PKG	QTY
US3A THRU US3M	SMC	3000



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